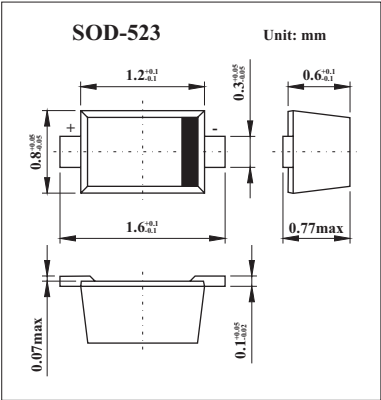


Silicon Epitaxial Planar Pin Diode

HVC131

■ Features

- Low capacitance.(C=0.8pF max)
- Low forward resistance. (rf=1.0 Ω max)



■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Value	Unit
Peak reverse voltage	V _{RM}	65	V
Reverse voltage	V _R	60	V
Forward current	I _F	100	mA
Power dissipation	P _d	150	mW
Junction temperature	T _j	125	℃
Storage temperature	T _{stg}	-55 to +125	℃

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Reverse current	I _R	V _R = 60 V			0.1	μ A
Reverse voltage	V _F	I _F = 10 mA			1.0	V
Capacitance	C	V _R = 1 V, f = 1 MHz			0.8	pF
Forward resistance	r _f	I _F = 10 mA, f = 100 MHz			1.0	Ω

■ Marking

Marking	P1
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